

GSDBAV19/20/21WS

High Voltage Switching Diodes

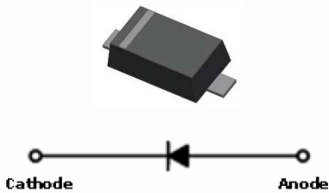
Product Description

High Voltage Switching Diode 200mW / 250V.

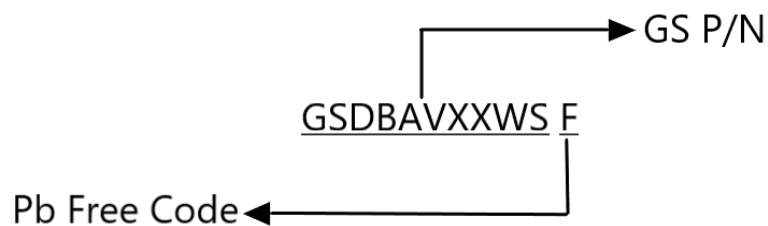
Features

- Flat Lead SOD-323 Small Outline Plastic Package
- Surface Device Type Mounting
- Moisture Sensitivity Level 1
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- Band Indicates Cathode

Marking Information

Part Number	Package	Part Marking	Equivalent Circuit Diagram
GSDBAV19WSF	SOD-323	S5	
GSDBAV20WSF	SOD-323	S6	
GSDBAV21WSF	SOD-323	S7	

Ordering Information



Part Number	Package	Quantity
GSDBAV19WSF	SOD-323	3,000 PCS
GSDBAV20WSF	SOD-323	3,000 PCS
GSDBAV21WSF	SOD-323	3,000 PCS

Absolute Maximum Ratings (T_A=25°C Unless Otherwise specified)

Symbol	Parameter	Value	Units
V _{RRM}	Maximum Repetitive Reverse Voltage	250	V
I _{F(AV)}	Average Rectified Forward Current	200	mA
I _{FSM}	Non-repetitive Peak Forward Current Pulse Width=1.0 Second Pulse Width=1.0 μsecond	1.0 4.0	A
P _D	Power Dissipation	200	mW
T _J	Operating Junction Temperature	+150	°C
T _{STG}	Storage Temperature Range	-65 to + 150	°C

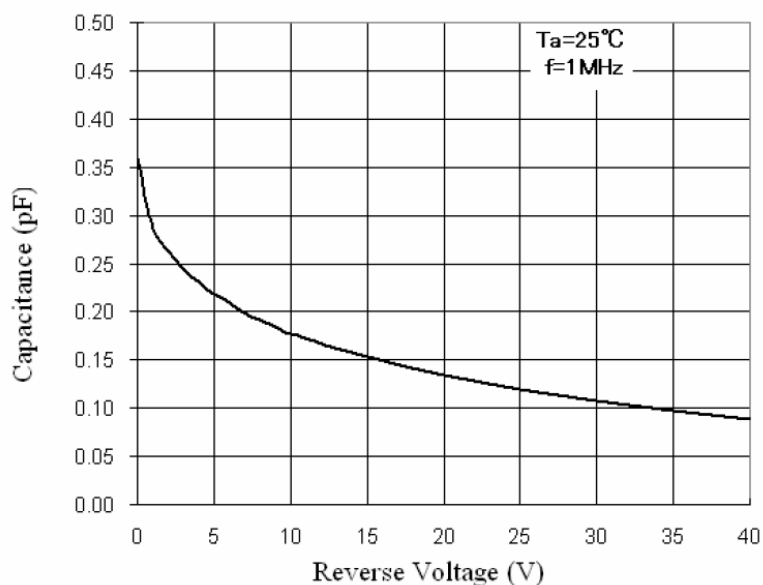
These ratings are limiting Values above which the serviceability of the diode may be impaired.

Electrical Characteristics (T_A=25°C Unless Otherwise specified)

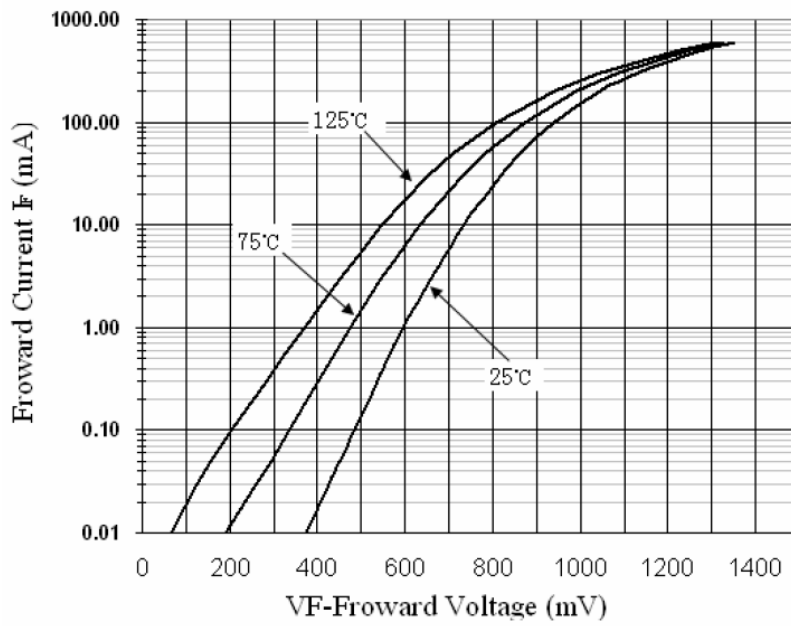
Symbol	Parameter	Test Condition	Min	Max	Units
V _F	Forward Voltage	I _F =100mA I _F =200mA	- -	1.0 1.25	V
I _R	Reverse Leakage Current GSDBAV19WS GSDBAV20WS GSDBAV21WS	V _R =100V V _R =150V V _R =200V	- - -	100 100 100	nA
B _V	Breakdown Voltage GSDBAV19WS GSDBAV20WS GSDBAV21WS	I _R =100μA	120 200 250	- - -	V
C	Capacitance	V _R =0V, f=1MHz	-	5.0	pF
T _{RR}	Reverse Recovery Time	I _F =I _R =30mA R _L =100Ω, I _{RR} =3mA	-	50	nS

Typical Characteristics

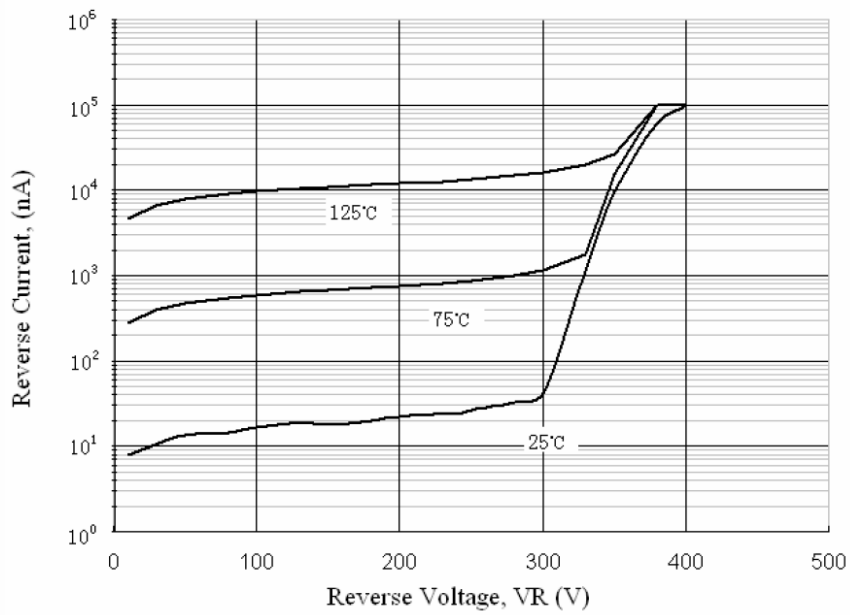
Total Capacitance



Forward Voltage vs Ambient Temperature

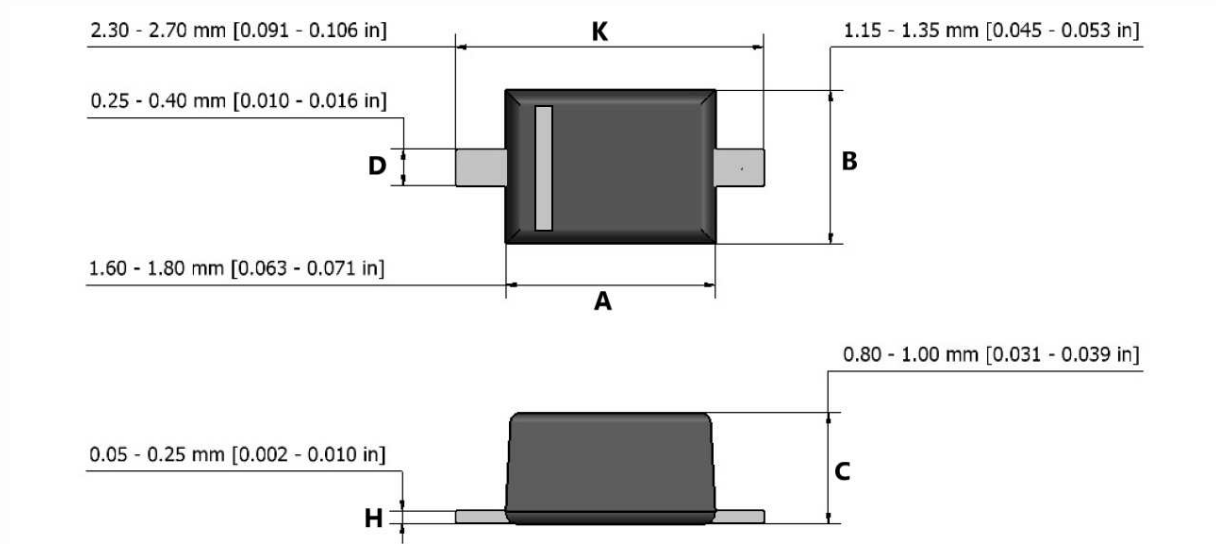


Reverse Current vs Reverse Voltage



Package Dimension

SOD-323



NOTES:

- The above package outline is similar to JEITA SC-90.





Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	1.6	1.8	0.063	0.071
B	1.15	1.35	0.045	0.053
C	0.8	1	0.031	0.039
D	0.25	0.4	0.01	0.016
H	0.05	0.25	0.002	0.01
K	2.3	2.7	0.091	0.106



Pin 1.CATHODE
Pin 2.ANODE

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